

RoHS

COMPLIANT



Integrated bypass diode for Solar cell Module

1.Features

- Schotty Barrier hight diode;
- Low thermal resistance;
- Lower forward voltage drop, low power loss;
- Isolate Package design, ideal for heat dispersion;
- High forward current capability;
- Excellent anti-humidity;
- Low profile package;
- High forward surge capability;

2.Mechanical Data

- Case: QC3Q;
- Terminals: Copper;
- High temperature soldering guaranteed;
 Heated-tool welding 260 °C,10seconds
- Marking: As marked on product;

3.Order Information

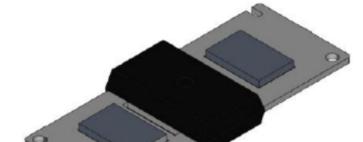
Package	QC3Q		
PVC tube	32pcs/ tube		
Inner Box	320pcs/ Inner box		
Carton	1600pcs/ Carton		

4.Typical Applications

For the protection of solar cell bypass box. Using DC forward current without reverse bias.

Maximum Ratings and Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.



QC3Q

Case: QC3Q

Dimensions in milimeters

Parameter		Symbol	QCF5045T	Unit
Maximum repetitive peak reverse voltage		V _{RRM}	45	Volt
Maximum working peak reverse voltage		V _{RWM}	45	Volt
Average rectified output current @ 60Hz sine wave, Ta=25℃		Io	50	Amps
Non-Repetitive Peak forward surge current @ 60Hz, single sine-wave load		I _{FSM}	450	Amps
Rating for fusing (t<8.3ms)		l ² t	840	A ² sec
Instantaneous forward voltage drop	@IF=10A @IF=20A @IF=30A @IF=50A	V _F	0.38Typ. 0.43max. 0.41Typ. 0.46max. 0.43Typ. 0.48max. 0.47 Typ. 0.52 max.	Volt
Reverse Current at Rated DC reverse Voltage	@Tj=25℃ @Tj=125℃	I _R	43Typ. 100max. 80.00 Typ. 100.00 max.	μA mA
Typical capacitance (1.0 MHz and Applic 5.0V D.C)		C _j	6600	pF
Typical thermal resistance		R _{OJ-c}	1.5	℃/ W
Storage Temperature		T _{STG}	-55 to +150	°C
Junction Temperature IN DC Forward M bias, t ≤1 h	ode, without reverse	TJ	-55 to +150	င

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5.Ratings and Characteristics Curves

(TA = 25℃ unless otherwise noted)

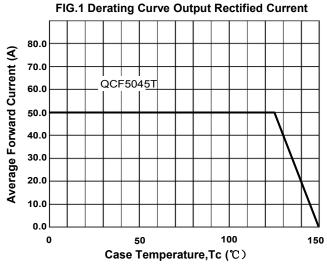


FIG.3 Maximum Non-Repetitive Peak Forward Surge Current per Diode

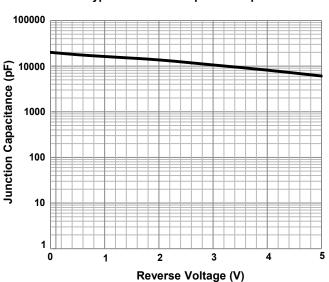
600

8.3ms single half sine-wave JEDEC method

100

1 10 100

Number of Cycles at 60Hz
FIG.5 Typical Junction Capacitance per Diode



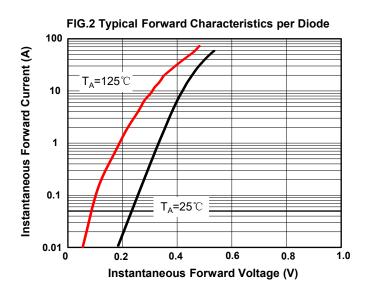
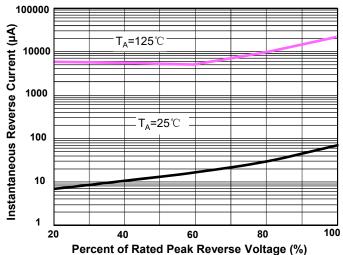


FIG.4 Typical Reverse Characteristics per Diode

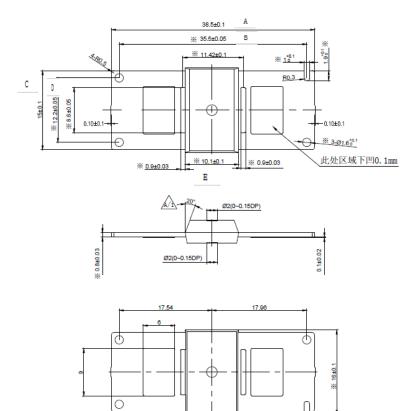


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1.2±0.05

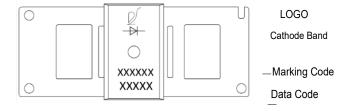


6. Dimensions



Dimensions	Inches		Millimeters	
	Min	Max	Min	Max
Α	1.512	1.520	38.40	38.60
В	1.396	1.400	35.45	35.55
С	0.587	0.595	14.90	15.10
D	0.476	0.484	12.10	12.30
Е	0.394	0.402	10.00	10.20
F	0.169	0.177	4.30	4.50

7.Part Marking System



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